

introducing processing gas comprising a gas comprising nitrogen atoms  
and a gas comprising hydrogen atoms into the process chamber;  
etching the organic film; and  
stopping the etching before the etching goes through the organic film.

7. (New) A method of etching according to claim 6, wherein the gas comprising nitrogen atoms constitute  $N_2$  and the gas comprising hydrogen atoms constitute  $H_2$ .
8. (New) A method of etching according to claim 6, wherein the processing gas further comprises Ar.
9. (New) A method of etching according to claim 7, wherein the processing gas further comprises Ar.
10. (New) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:  
placing the workpiece in a hermetically sealed process chamber;  
introducing processing gas into the process chamber;  
pressurizing the process chamber to a pressure equal to or higher than  
500 mTorr;  
etching the organic film; and  
stopping the etching before the etching goes through the organic film.
11. (New) A method of etching according to claim 10, wherein the processing gas comprises a gas comprising nitrogen atoms and a gas comprising hydrogen atoms.

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12. (New) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:
- placing the workpiece in a hermetically sealed process chamber;
  - introducing processing gas comprising a gas comprising nitrogen atoms and a gas comprising hydrogen atoms into the process chamber;
  - pressurizing the process chamber to a pressure between 500 - 800 mTorr;
  - etching the organic film; and
  - stopping the etching before the etching goes through the organic film.
13. (New) A method of etching according to claim 12, wherein the gas comprising nitrogen atoms constitute  $N_2$  and the gas comprising hydrogen atoms constitute  $H_2$ .
14. (New) A method of etching according to claim 12, wherein the processing gas further comprises Ar.
15. (New) A method of etching according to claim 13, wherein the processing gas further comprises Ar.

**IN THE DRAWINGS:**

Subject to the approval of the Examiner, please amend the drawings as set forth in the Request for Approval of Drawing Changes submitted herewith.

**REMARKS**

Applicants respectfully request that this Preliminary Amendment be entered prior to the examination of the application. Applicant respectfully requests favorable consideration of this application.

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